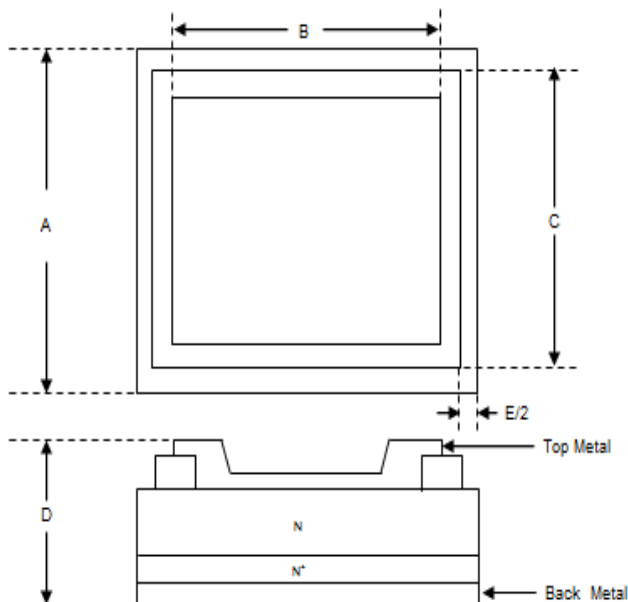


Planar Schottky Barrier Diode Wafer (PSBD)



Item	Dimensions	
	um	mil
Die Size (A)	295	12
Top Metal Pad Size (B)	170	6.69
Passivation Seal (C)	255	10
Wafer Thickness (D)	150±20	6.0
Scribe Line Width (E)	40	1.57
Other Informations		
Wafer Size	6"	
Gross Die	187300	
Top Metal	Al	
Back Metal	Sn	

Electrical Characteristics @TA=25°C

Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.1mA	V_{RRM}	40	43	V
Maximum Average Forward Rectified Current	I_o	0.1	-	A
Forward Voltage Drop, @ $I_F=0.1mA$ @ $I_F=1mA$ @ $I_F=10mA$ @ $I_F=30mA$ @ $I_F=100mA$	V_F	0.24 0.32 0.4 0.46 0.54	-	V
Maximum Reverse Current at Rated V_{RRM}	I_R	3	-	μA
Total Capacitance	C_T	10	-	pF
Operating Temperature Range	T_J	-50 to +125	-	°C
Storage Temperature Range	T_{STG}	-50 to +125	-	°C